Docket No.: 20506/0203830-US0

(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Euijoon Yoon et al.

Application No.: 10/563,854

Confirmation No.: N/A

Filed: January 6, 2006

Art Unit: N/A

For: GROWTH METHOD FOR NITRIDE

Examiner: Not Yet Assigned

SEMICONDUCTOR EPITAXIAL LAYERS

SECOND PRELIMINARY AMENDMENT

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

Prior to examination on the merits, please amend the above-identified U.S. patent application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks/Arguments begin on page 6 of this paper.